

INFORMATION DISCLOSURE CITATION MPEP-1449	CUSTOMER NUMBER 26615	ATTORNEY'S DKT No. H1130	APPLICATION No. 10/614,177	
		APPLICANT(s) Bin YU et al.		
		FILING DATE July 8, 2003	GROUP 2811	


U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
RR	2002/0137271	9-26-02	Forbes et al.			
I	5,411,905	5-2-95	Acovic et al.			
I	2003/0178670	9-25-03	Fried et al.			
RR	2002/0072170	6-13-02	Lam			

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

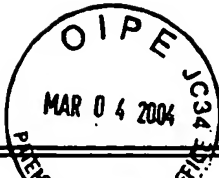
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	

EXAMINER <i>H. Rose</i>	DATE CONSIDERED 11/9/04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

INFORMATION DISCLOSURE CITATION PTO-1449		 26615 <small>PATENT TRADEMARK OFFICE</small>	ATTORNEY'S DKT No. H1130		APPLICATION No. Unassigned		
			APPLICANT(S) Bin YU et al.				
			FILING DATE July 8, 2003		GROUP Unassigned		
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						Yes	No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
KR	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.						
	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.						
	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.						
	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.						
KR	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.						
EXAMINER <i>H. Rose</i>				DATE CONSIDERED <i>11/9/04</i>			

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						Yes	No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
RR	Copy of co-pending U.S. Patent Application No. 10/770,010; by Yider Wu et al., filed February 3, 2004 entitled: "Non-Volatile Memory Device," 21 page specification, 11 sheets of drawings.						
RR	Copy of co-pending U.S. Patent Application No. 10/632,971; by Ming-Ren Lin et al., filed August 4, 2003 entitled: "FinFET Flash Memory," 11 page specification, 9 sheets of drawings.						
EXAMINER <i>K. Rose</i>				DATE CONSIDERED 11/9/04			

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INFORMATION DISCLOSURE CITATION PTO-1449 SEP 15 2004	CUSTOMER NUMBER 45114	ATTORNEY'S DKT No. H1130	APPLICATION No. 10/614,177
		APPLICANT(S) Bin Yu et al.	
		FILING DATE July 8, 2003	GROUP 2811

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

RR	Copy of co-pending U.S. Patent Application No. 10/929,538 by Yu et al., filed August 31, 2004, entitled "Non-Volatile Memory Device", 25 pages

EXAMINER <i>Kushy Rose</i>	DATE CONSIDERED 11/9/04
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